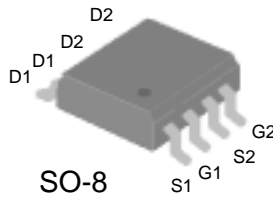


**COMPLEMENTARY N AND P-CHANNEL ENHANCEMENT-MODE POWER MOSFETS**

- Simple drive requirement
- Low on-resistance
- Fast switching performance

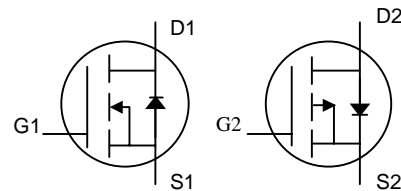


N-Ch	$BV_{DSS}$	60V
	$R_{DS(ON)}$	36m $\Omega$
	$I_D$	6A
P-Ch	$BV_{DSS}$	-60V
	$R_{DS(ON)}$	72m $\Omega$
	$I_D$	-4.2A

**Description**

Power MOSFETs from Silicon Standard provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The SO-8 package is widely preferred for commercial and industrial surface mount applications and is well suited for low-voltage applications such as DC/DC converters.


**Absolute Maximum Ratings**

Symbol	Parameter	Rating		Units
		N-channel	P-channel	
$V_{DS}$	Drain-Source Voltage	60	-60	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	$\pm 20$	V
$I_D @ T_A=25^\circ C$	Continuous Drain Current <sup>3</sup>	6	-4.2	A
$I_D @ T_A=70^\circ C$	Continuous Drain Current <sup>3</sup>	4.7	-3.3	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	30	-30	A
$P_D @ T_A=25^\circ C$	Total Power Dissipation	2.0		W
	Linear Derating Factor	0.016		W/ $^\circ C$
$T_{STG}$	Storage Temperature Range	-55 to 150		$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150		$^\circ C$

**Thermal Data**

Symbol	Parameter	Value	Unit
Rthj-a	Thermal Resistance Junction-ambient <sup>3</sup>	Max. 62.5	$^\circ C/W$

**N-channel Electrical Characteristics @  $T_j=25^\circ\text{C}$ (unless otherwise specified)**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	60	-	-	V
$\Delta BV_{DSS}/\Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to $25^\circ\text{C}, I_D=1\text{mA}$	-	0.04	-	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V, I_D=5A$	-	-	36	$\text{m}\Omega$
		$V_{GS}=4.5V, I_D=3A$	-	-	42	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1	-	3	V
$g_{fs}$	Forward Transconductance	$V_{DS}=10V, I_D=5A$	-	8	-	S
$I_{DSS}$	Drain-Source Leakage Current ( $T_j=25^\circ\text{C}$ )	$V_{DS}=60V, V_{GS}=0V$	-	-	1	$\mu A$
	Drain-Source Leakage Current ( $T_j=70^\circ\text{C}$ )	$V_{DS}=48V, V_{GS}=0V$	-	-	25	$\mu A$
$I_{GSS}$	Gate-Source Leakage	$V_{GS}=\pm 20V$	-	-	$\pm 100$	nA
$Q_g$	Total Gate Charge <sup>2</sup>	$I_D=5A$	-	18	29	nC
$Q_{gs}$	Gate-Source Charge	$V_{DS}=48V$	-	5	-	nC
$Q_{gd}$	Gate-Drain ("Miller") Charge	$V_{GS}=4.5V$	-	10	-	nC
$t_{d(on)}$	Turn-on Delay Time <sup>2</sup>	$V_{DS}=30V$	-	10	-	ns
$t_r$	Rise Time	$I_D=1A$	-	6	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=3.3\Omega, V_{GS}=10V$	-	32	-	ns
$t_f$	Fall Time	$R_D=30\Omega$	-	10	-	ns
$C_{iss}$	Input Capacitance	$V_{GS}=0V$	-	1670	2670	pF
$C_{oss}$	Output Capacitance	$V_{DS}=25V$	-	160	-	pF
$C_{riss}$	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	117	-	pF

**Source-Drain Diode**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{SD}$	Forward On Voltage <sup>2</sup>	$I_S=1.7A, V_{GS}=0V$	-	-	1.2	V
$t_{rr}$	Reverse Recovery Time <sup>2</sup>	$I_S=5A, V_{GS}=0V$	-	34	-	ns
$Q_{rr}$	Reverse Recovery Charge	$di/dt=100A/\mu s$	-	48	-	nC

**P-channel Electrical Characteristics @  $T_j=25^{\circ}\text{C}$ (unless otherwise specified)**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-60	-	-	V
$\Delta BV_{DSS}/\Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to $25^{\circ}\text{C}, I_D=-1\text{mA}$	-	-0.04	-	$\text{V}/^{\circ}\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=-10V, I_D=-4A$	-	-	72	$\text{m}\Omega$
		$V_{GS}=-4.5V, I_D=-3A$	-	-	88	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-	-3	V
$g_{fs}$	Forward Transconductance	$V_{DS}=-10V, I_D=-4A$	-	6	-	S
$I_{DSS}$	Drain-Source Leakage Current ( $T=25^{\circ}\text{C}$ )	$V_{DS}=-60V, V_{GS}=0V$	-	-	-1	$\mu A$
	Drain-Source Leakage Current ( $T=70^{\circ}\text{C}$ )	$V_{DS}=-48V, V_{GS}=0V$	-	-	-25	$\mu A$
$I_{GSS}$	Gate-Source Leakage	$V_{GS}=\pm 20V$	-	-	$\pm 100$	nA
$Q_g$	Total Gate Charge <sup>2</sup>	$I_D=-4A$	-	21	34	nC
$Q_{gs}$	Gate-Source Charge	$V_{DS}=-48V$	-	5	-	nC
$Q_{gd}$	Gate-Drain ("Miller") Charge	$V_{GS}=-4.5V$	-	9	-	nC
$t_{d(on)}$	Turn-on Delay Time <sup>2</sup>	$V_{DS}=-30V$	-	12	-	ns
$t_r$	Rise Time	$I_D=-1A$	-	6	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=3.3\Omega, V_{GS}=-10V$	-	82	-	ns
$t_f$	Fall Time	$R_D=30\Omega$	-	36	-	ns
$C_{iss}$	Input Capacitance	$V_{GS}=0V$	-	1780	2850	pF
$C_{oss}$	Output Capacitance	$V_{DS}=-25V$	-	157	-	pF
$C_{rss}$	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	130	-	pF

**Source-Drain Diode**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{SD}$	Forward On Voltage <sup>2</sup>	$I_S=-1.7A, V_{GS}=0V$	-	-	-1.2	V
$t_{rr}$	Reverse Recovery Time <sup>2</sup>	$I_S=-4A, V_{GS}=0V$	-	43	-	ns
$Q_{rr}$	Reverse Recovery Charge	$dI/dt=-100A/\mu s$	-	87	-	nC

**Notes:**

1. Pulse width limited by max. junction temperature.
2. Pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
3. Surface mounted on  $1\text{ in}^2$  copper pad of FR4 board;  $135^{\circ}\text{C}/\text{W}$  when mounted on min. copper pad.

## N-channel

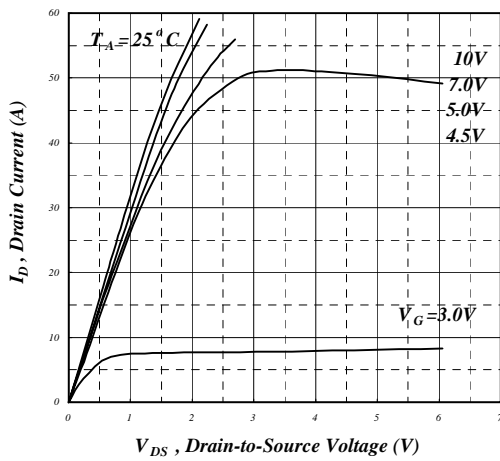


Fig 1. Typical Output Characteristics

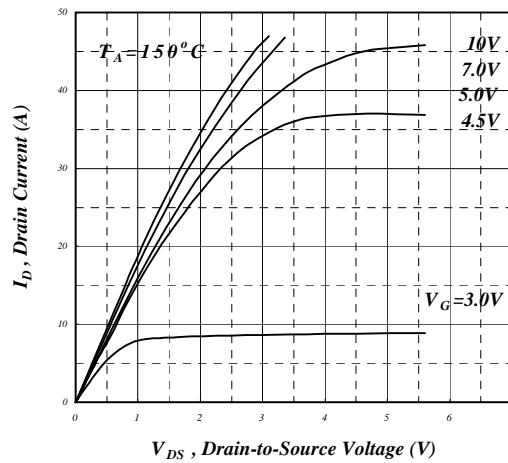


Fig 2. Typical Output Characteristics

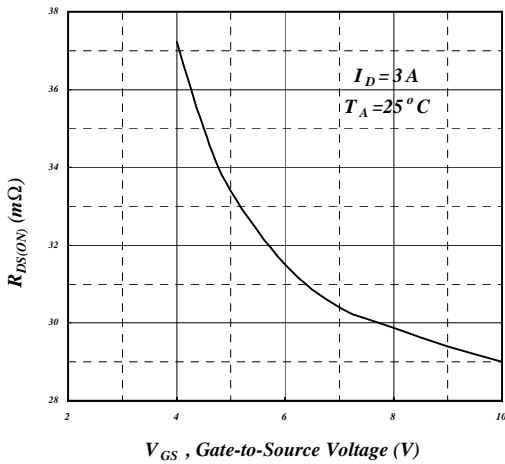


Fig 3. On-Resistance vs. Gate Voltage

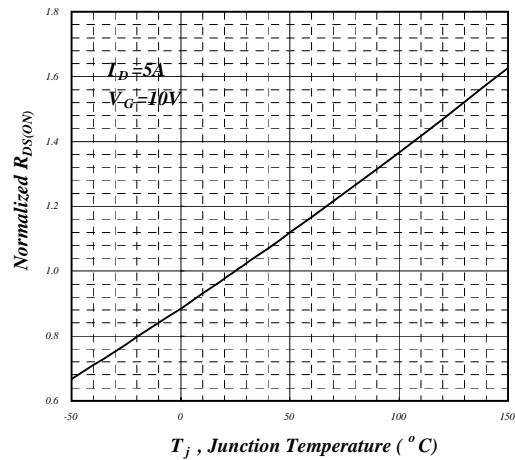


Fig 4. Normalized On-Resistance v.s. Junction Temperature

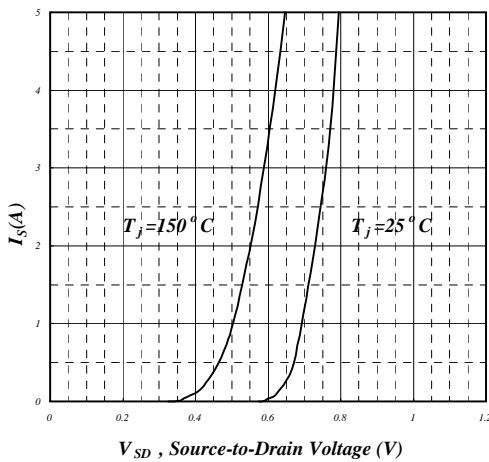


Fig 5. Forward Characteristic of Reverse Diode

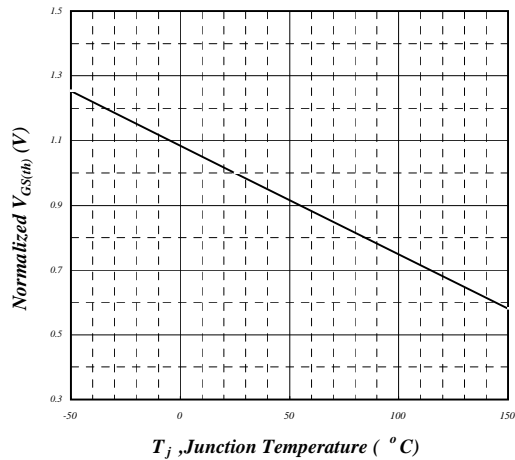


Fig 6. Gate Threshold Voltage vs. Junction Temperature

## N-channel

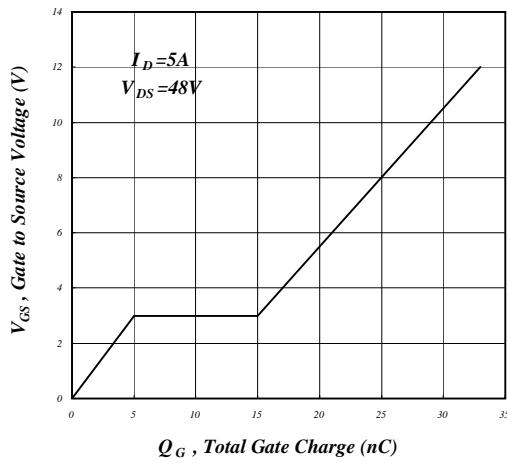


Fig 7. Gate Charge Characteristics

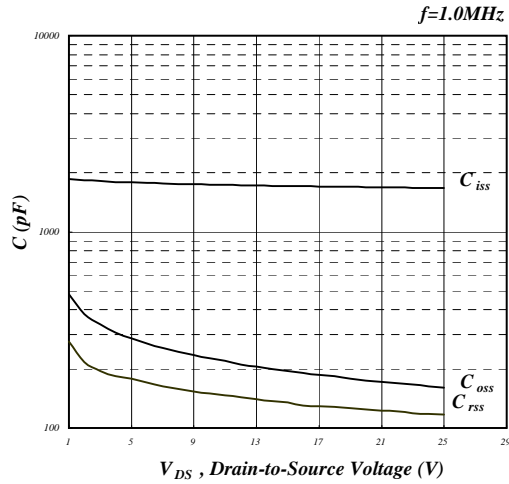


Fig 8. Typical Capacitance Characteristics

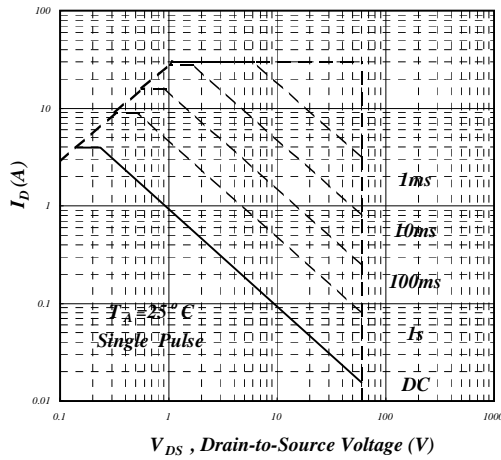


Fig 9. Maximum Safe Operating Area

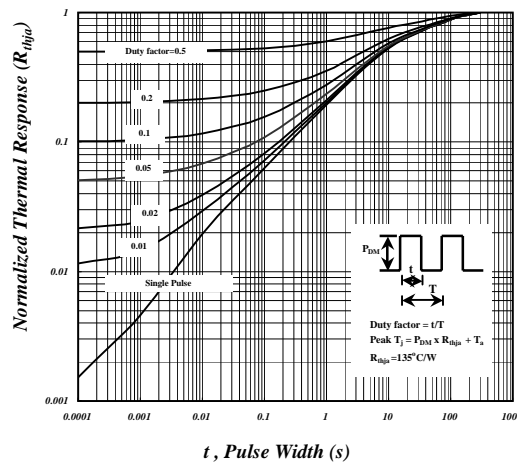


Fig 10. Effective Transient Thermal Impedance

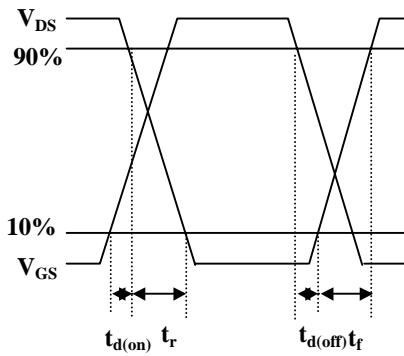


Fig 11. Switching Time Waveform

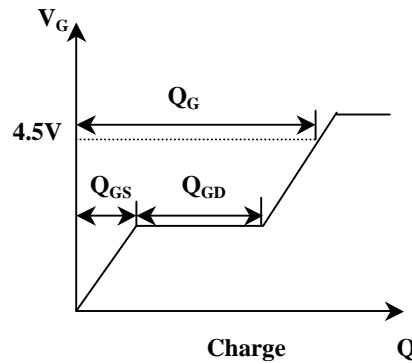


Fig 12. Gate Charge Waveform

## P-channel

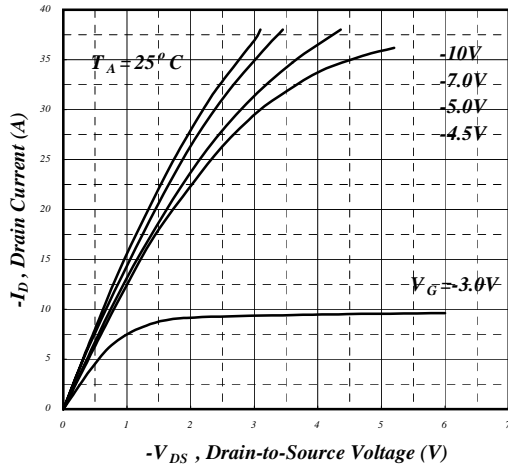


Fig 1. Typical Output Characteristics

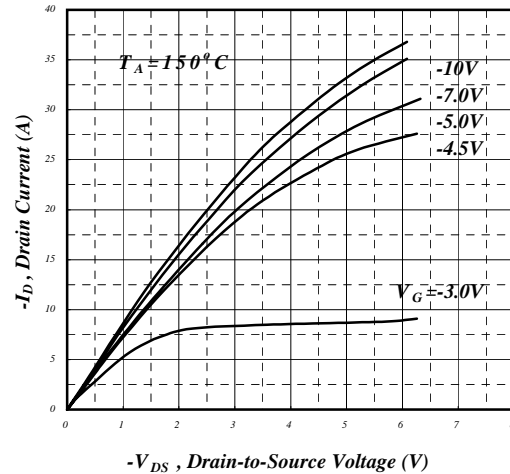


Fig 2. Typical Output Characteristics

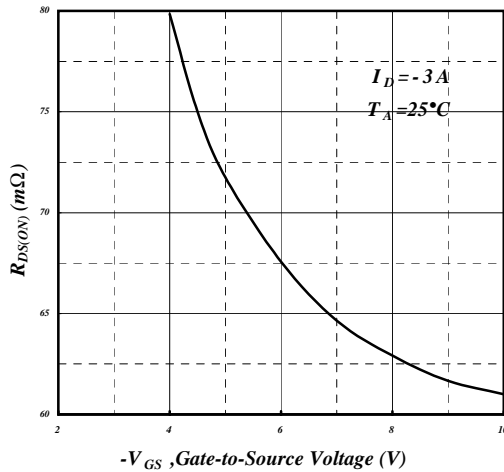


Fig 3. On-Resistance vs. Gate Voltage

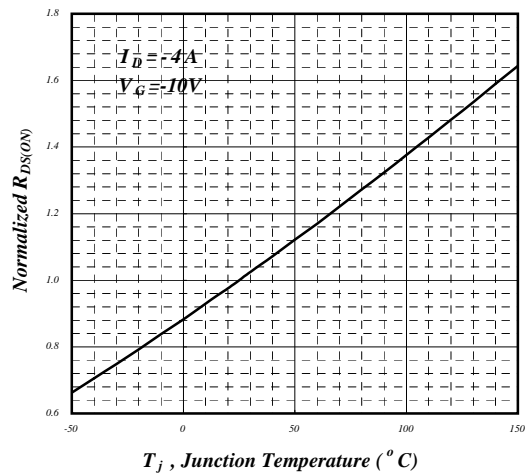


Fig 4. Normalized On-Resistance vs. Junction Temperature

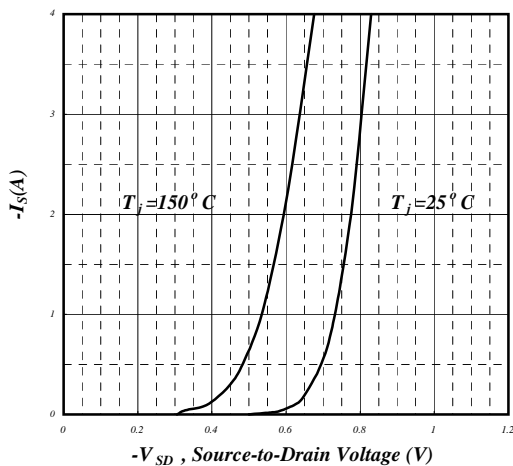


Fig 5. Forward Characteristic of Reverse Diode

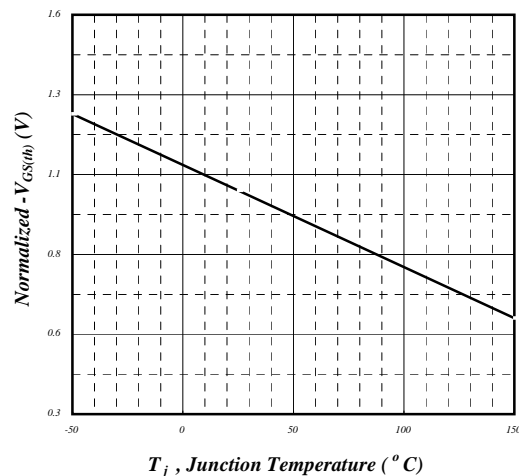
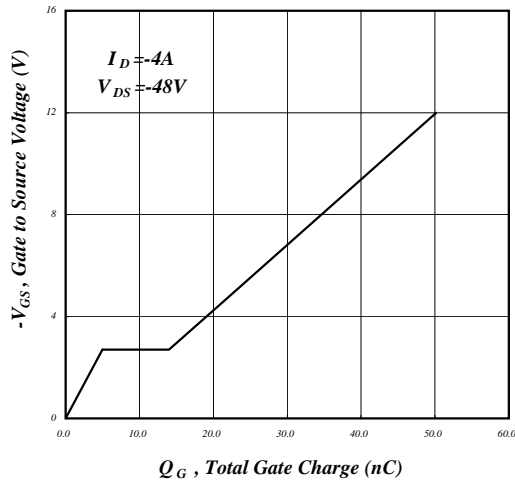
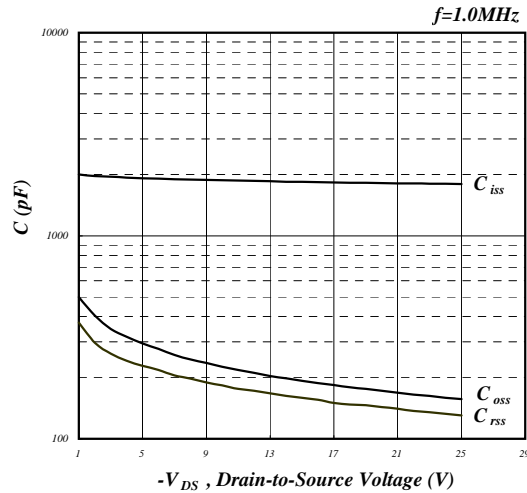


Fig 6. Gate Threshold Voltage vs. Junction Temperature

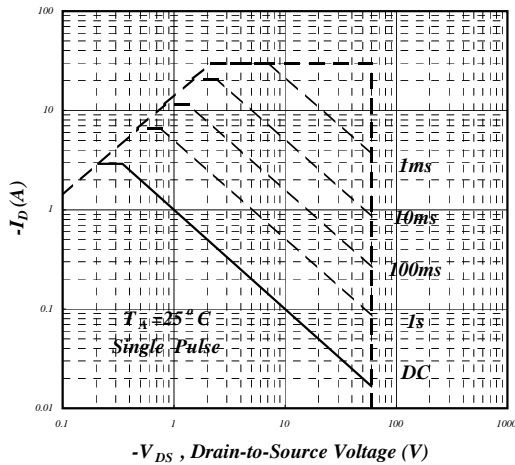
## P-channel



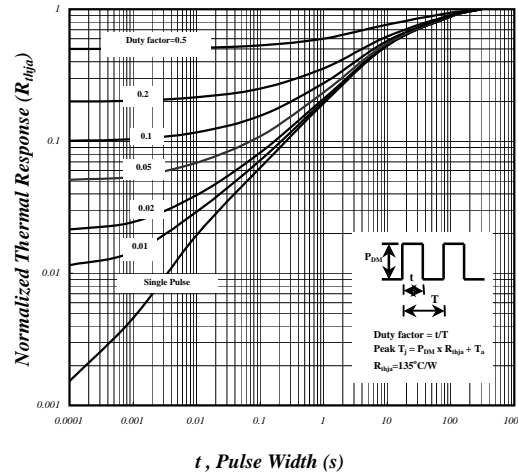
**Fig 7. Gate Charge Characteristics**



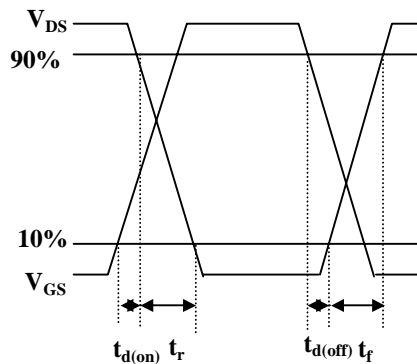
**Fig 8. Typical Capacitance Characteristics**



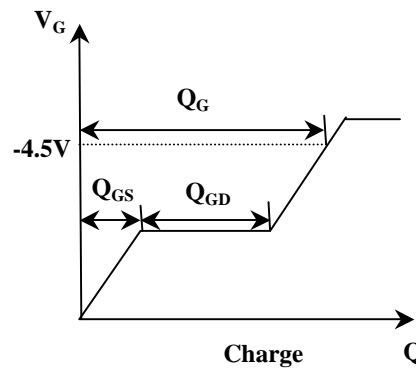
**Fig 9. Maximum Safe Operating Area**



**Fig 10. Effective Transient Thermal Impedance**



**Fig 11. Switching Time Waveform**



**Fig 12. Gate Charge Waveform**

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